

# FMG2G100US60

## Molding Type Module

### General Description

Fairchild's Insulated Gate Bipolar Transistor (IGBT) power modules provide low conduction and switching losses as well as short circuit ruggedness. They are designed for applications such as motor control, uninterrupted power supplies (UPS) and general inverters where short circuit ruggedness is a required feature.

### Features

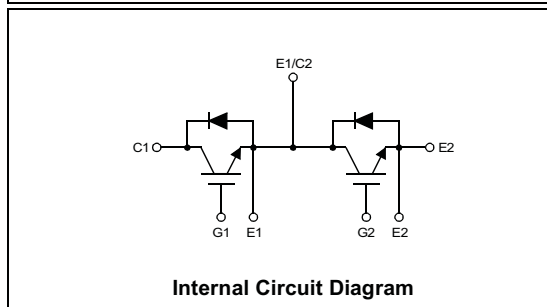
- UL Certified No. E209204
- Short Circuit rated 10us @  $T_C = 100^\circ\text{C}$ ,  $V_{GE} = 15\text{V}$
- High Speed Switching
- Low Saturation Voltage :  $V_{CE(sat)} = 2.2\text{V}$  @  $I_C = 100\text{A}$
- High Input Impedance
- Fast & Soft Anti-Parallel FWD

### Application

- AC & DC Motor Controls
- General Purpose Inverters
- Robotics
- Servo Controls
- UPS



Package Code : 7PM-GA



Internal Circuit Diagram

### Absolute Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Description	FMG2G100US60	Units
$V_{CES}$	Collector-Emitter Voltage	600	V
$V_{GES}$	Gate-Emitter Voltage	$\pm 20$	V
$I_C$	Collector Current @ $T_C = 25^\circ\text{C}$	100	A
$I_{CM(1)}$	Pulsed Collector Current	200	A
$I_F$	Diode Continuous Forward Current @ $T_C = 100^\circ\text{C}$	100	A
$I_{FM}$	Diode Maximum Forward Current	200	A
$T_{SC}$	Short Circuit Withstand Time @ $T_C = 100^\circ\text{C}$	10	us
$P_D$	Maximum Power Dissipation @ $T_C = 25^\circ\text{C}$	400	W
$T_J$	Operating Junction Temperature	-40 to +150	$^\circ\text{C}$
$T_{stg}$	Storage Temperature Range	-40 to +125	$^\circ\text{C}$
$V_{iso}$	Isolation Voltage @ AC 1minute	2500	V
Mounting Torque	Power Terminals Screw : M5	2.0	N.m
	Mounting Screw : M5	2.0	N.m

**Notes :**

(1) Repetitive rating : Pulse width limited by max. junction temperature

## Electrical Characteristics of IGBT T<sub>C</sub> = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
<b>Off Characteristics</b>						
BV <sub>CES</sub>	Collector-Emitter Breakdown Voltage	V <sub>GE</sub> = 0V, I <sub>C</sub> = 250uA	600	--	--	V
ΔBV <sub>CES</sub> /ΔT <sub>J</sub>	Temperature Coeff. of Breakdown Voltage	V <sub>GE</sub> = 0V, I <sub>C</sub> = 1mA	--	0.6	--	V/°C
I <sub>CES</sub>	Collector Cut-Off Current	V <sub>CE</sub> = V <sub>CES</sub> , V <sub>GE</sub> = 0V	--	--	250	uA
I <sub>GES</sub>	G-E Leakage Current	V <sub>GE</sub> = V <sub>GES</sub> , V <sub>CE</sub> = 0V	--	--	± 100	nA
<b>On Characteristics</b>						
V <sub>GE(th)</sub>	G-E Threshold Voltage	V <sub>GE</sub> = 0V, I <sub>C</sub> = 100mA	5.0	6.0	8.5	V
V <sub>CE(sat)</sub>	Collector to Emitter Saturation Voltage	I <sub>C</sub> = 100A, V <sub>GE</sub> = 15V	--	2.2	2.8	V
<b>Dynamic Characteristics</b>						
C <sub>ies</sub>	Input Capacitance	V <sub>CE</sub> = 30V, V <sub>GE</sub> = 0V, f = 1MHz	--	10840	--	pF
C <sub>oes</sub>	Output Capacitance		--	963	--	pF
C <sub>res</sub>	Reverse Transfer Capacitance		--	228	--	pF
<b>Switching Characteristics</b>						
t <sub>d(on)</sub>	Turn-On Delay Time	V <sub>CC</sub> = 300 V, I <sub>C</sub> = 100A, R <sub>G</sub> = 2.4Ω, V <sub>GE</sub> = 15V Inductive Load, T <sub>C</sub> = 25°C	--	25	--	ns
t <sub>r</sub>	Rise Time		--	50	--	ns
t <sub>d(off)</sub>	Turn-Off Delay Time		--	80	--	ns
t <sub>f</sub>	Fall Time		--	110	200	ns
E <sub>on</sub>	Turn-On Switching Loss		--	1.6	--	mJ
E <sub>off</sub>	Turn-Off Switching Loss	--	2.4	--	mJ	
E <sub>ts</sub>	Total Switching Loss	--	4.0	--	mJ	
t <sub>d(on)</sub>	Turn-On Delay Time	V <sub>CC</sub> = 300 V, I <sub>C</sub> = 100A, R <sub>G</sub> = 2.4Ω, V <sub>GE</sub> = 15V Inductive Load, T <sub>C</sub> = 125°C	--	25	--	ns
t <sub>r</sub>	Rise Time		--	60	--	ns
t <sub>d(off)</sub>	Turn-Off Delay Time		--	80	--	ns
t <sub>f</sub>	Fall Time		--	240	--	ns
E <sub>on</sub>	Turn-On Switching Loss		--	1.7	--	mJ
E <sub>off</sub>	Turn-Off Switching Loss	--	4.3	--	mJ	
E <sub>ts</sub>	Total Switching Loss	--	6.0	--	mJ	
T <sub>sc</sub>	Short Circuit Withstand Time	V <sub>CC</sub> = 300 V, V <sub>GE</sub> = 15V @ T <sub>C</sub> = 100°C	10	--	--	us
Q <sub>g</sub>	Total Gate Charge	V <sub>CE</sub> = 300 V, I <sub>C</sub> = 100A, V <sub>GE</sub> = 15V	--	425	500	nC
Q <sub>ge</sub>	Gate-Emitter Charge		--	80	--	nC
Q <sub>gc</sub>	Gate-Collector Charge		--	200	--	nC

**Electrical Characteristics of DIODE**  $T_C = 25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units	
$V_{FM}$	Diode Forward Voltage	$I_F = 100\text{A}$	$T_C = 25^\circ\text{C}$	--	1.9	2.8	V
			$T_C = 100^\circ\text{C}$	--	1.8	--	
$t_{rr}$	Diode Reverse Recovery Time		$T_C = 25^\circ\text{C}$	--	90	130	ns
			$T_C = 100^\circ\text{C}$	--	130	--	
$I_{rr}$	Diode Peak Reverse Recovery Current	$I_F = 100\text{A}$ $di / dt = 200 \text{ A/us}$	$T_C = 25^\circ\text{C}$	--	9	12	A
			$T_C = 100^\circ\text{C}$	--	12	--	
$Q_{rr}$	Diode Reverse Recovery Charge		$T_C = 25^\circ\text{C}$	--	405	790	nC
			$T_C = 100^\circ\text{C}$	--	780	--	

**Thermal Characteristics**

Symbol	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case (IGBT Part, per 1/2 Module)	--	0.31	$^\circ\text{C/W}$
$R_{\theta JC}$	Junction-to-Case (DIODE Part, per 1/2 Module)	--	0.7	$^\circ\text{C/W}$
$R_{\theta CS}$	Case-to-Sink (Conductive grease applied)	0.05	--	$^\circ\text{C/W}$
Weight	Weight of Module	--	190	g

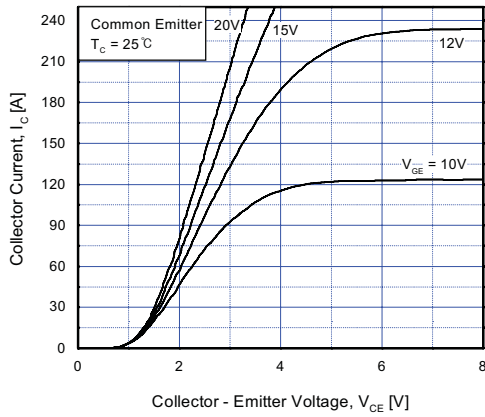


Fig 1. Typical Output Characteristics

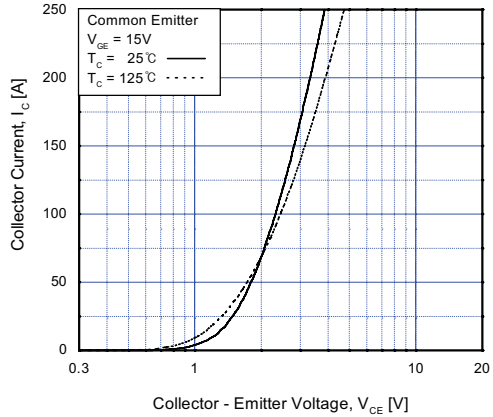


Fig 2. Typical Saturation Voltage Characteristics

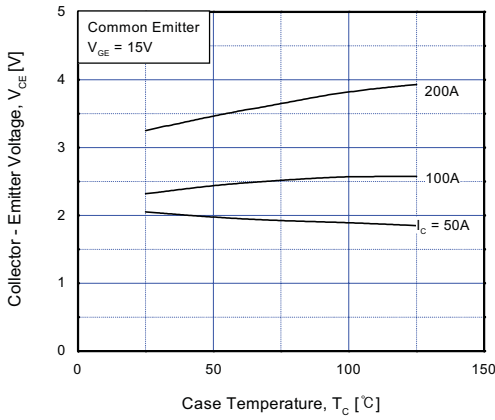


Fig 3. Saturation Voltage vs. Case Temperature at Variant Current Level

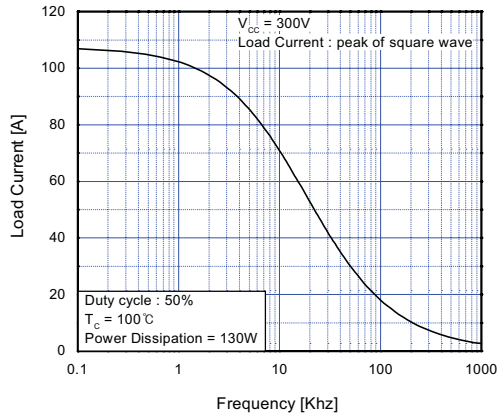


Fig 4. Load Current vs. Frequency

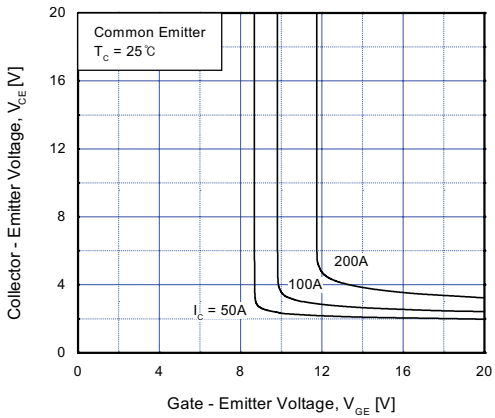


Fig 5. Saturation Voltage vs.  $V_{GE}$

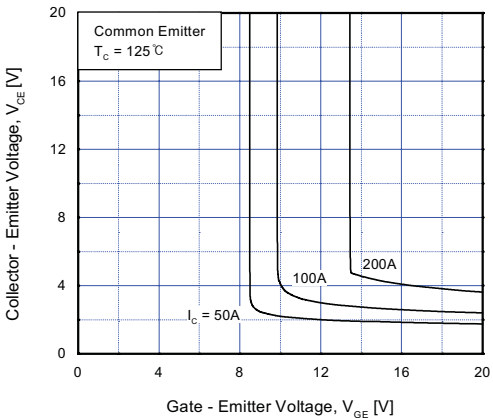


Fig 6. Saturation Voltage vs.  $V_{GE}$

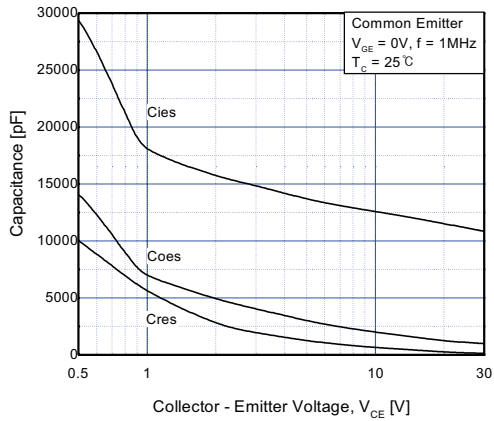


Fig 7. Capacitance Characteristics

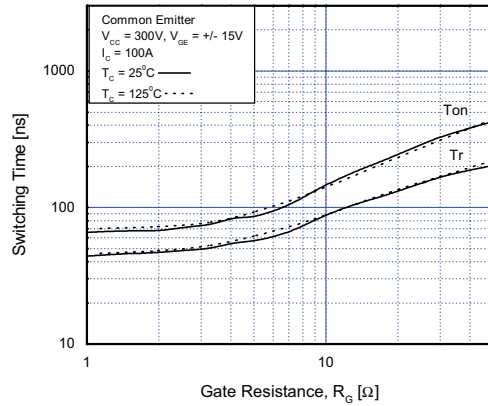


Fig 8. Turn-On Characteristics vs. Gate Resistance

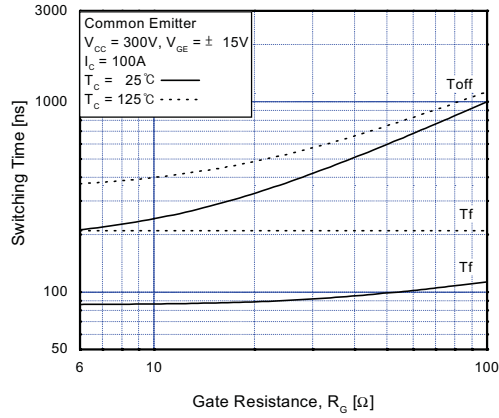


Fig 9. Turn-Off Characteristics vs. Gate Resistance

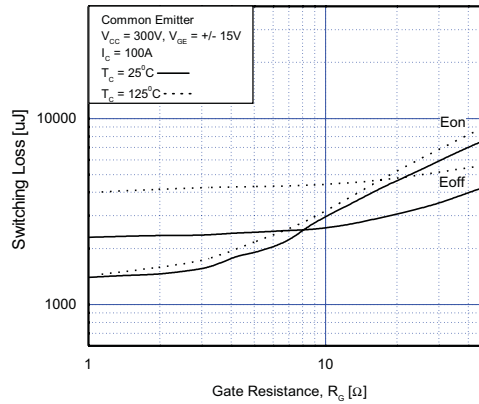


Fig 10. Switching Loss vs. Gate Resistance

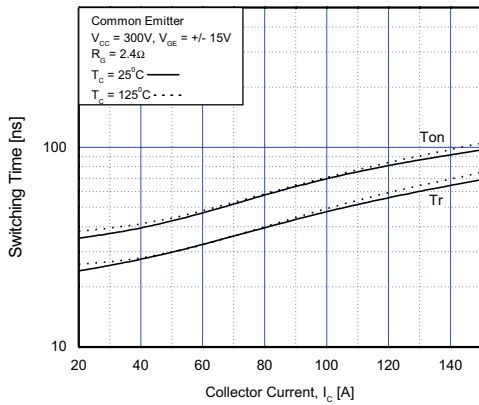


Fig 11. Turn-On Characteristics vs. Collector Current

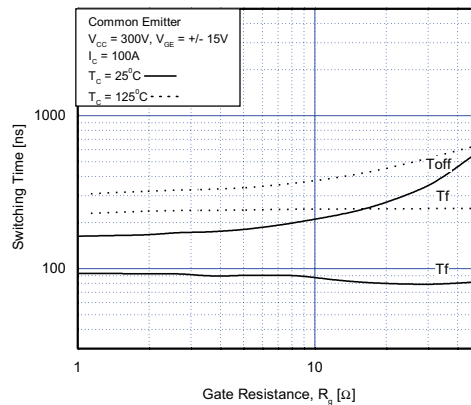


Fig 12. Turn-Off Characteristics vs. Collector Current

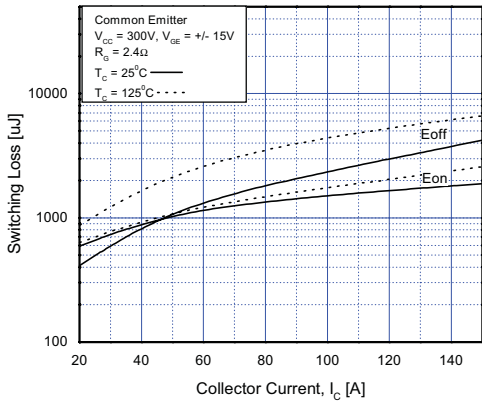


Fig 13. Switching Loss vs. Collector Current

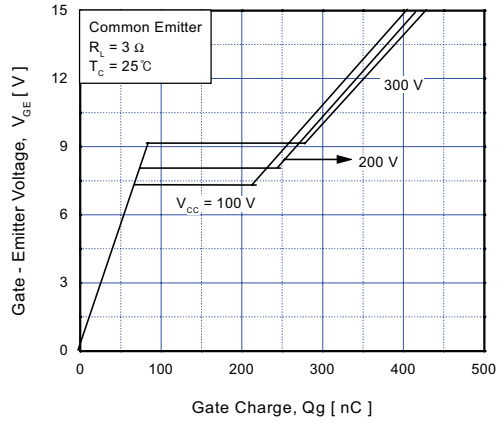


Fig 14. Gate Charge Characteristics

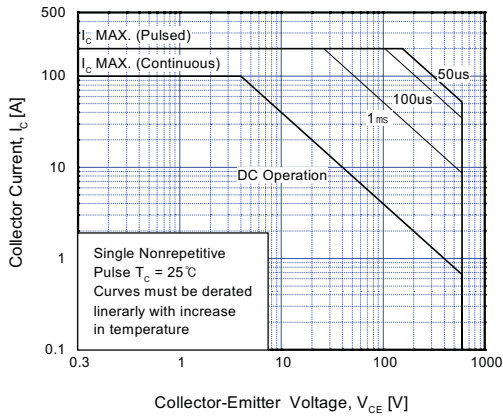


Fig 15. SOA Characteristics

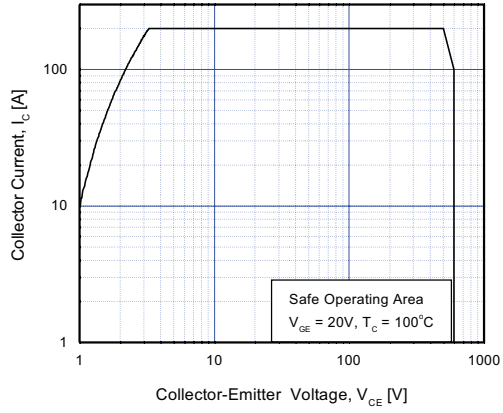


Fig 16. Turn-Off SOA Characteristics

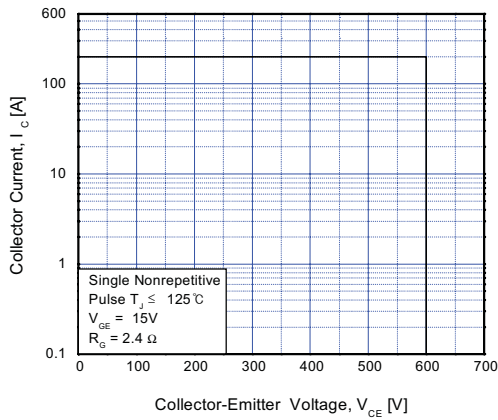


Fig 17. RBSOA Characteristics

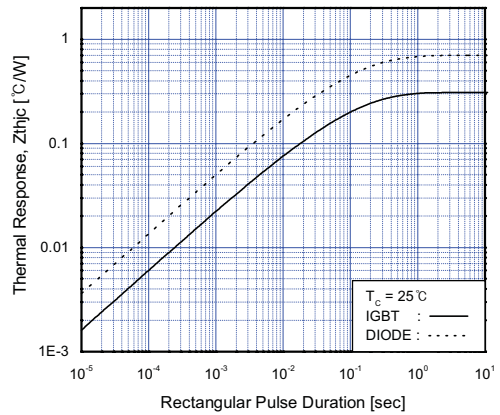


Fig 18. Transient Thermal Impedance

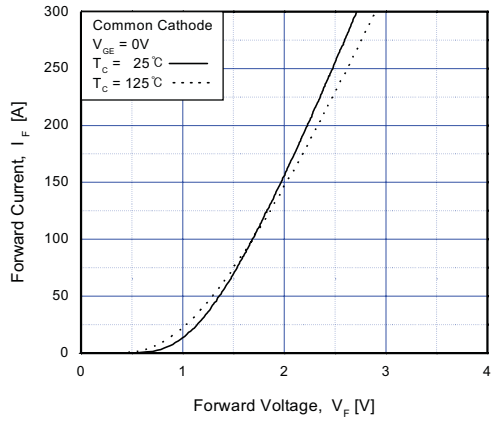


Fig 19. Forward Characteristics

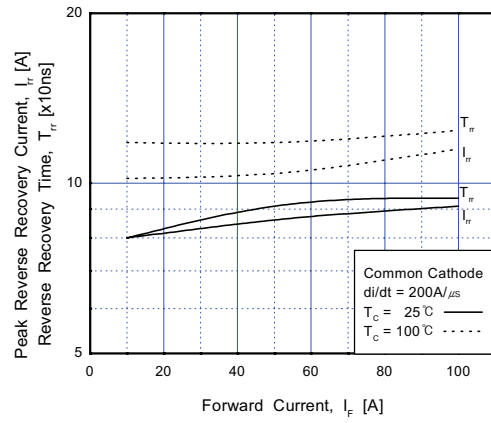
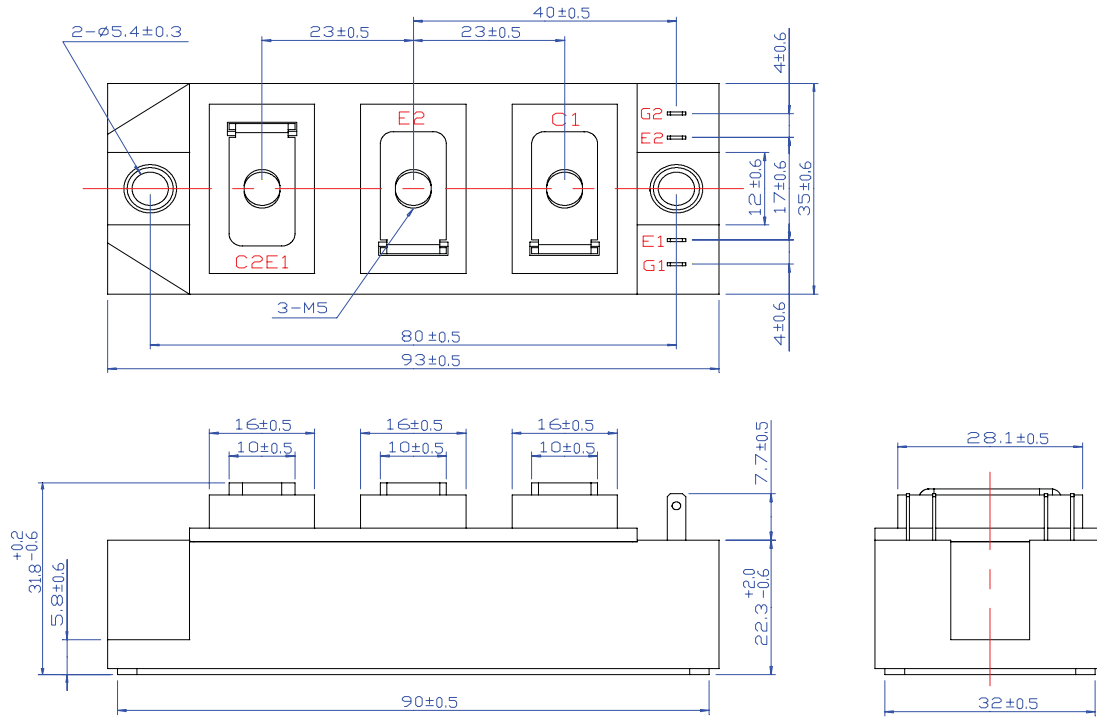


Fig 20. Reverse Recovery Characteristics

# Package Dimension

## 7PM-GA



FMG2G100US60

Dimensions in Millimeters



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DenseTrench <sup>™</sup>	GTO <sup>™</sup>	Power247 <sup>™</sup>	SuperSOT <sup>™</sup> -6	
DO <sub>ME</sub> <sup>™</sup>	HiSeC <sup>™</sup>	PowerTrench <sup>®</sup>	SuperSOT <sup>™</sup> -8	
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E <sup>2</sup> C <sub>MOS</sub> <sup>™</sup>	LittleFET <sup>™</sup>	QS <sup>™</sup>	TruTranslation <sup>™</sup>	
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